

L Number	Hits	Search Text	DB	Time stamp
1	110	gate adj electrode near5 doped adj silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 20:55
2	44	(gate adj electrode near5 doped adj silicon) and 257/\$5.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 21:18
3	133	(tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 21:20
4	1	(tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. and silicon adj oxynitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 21:21
-	1211	(("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 20:52
-	1399	(("257/410") or ("257/411") or ("257/412")).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 11:30
-	1078	((("257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649"))).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 11:31
-	3605	((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or (((("257/410") or ("257/411") or ("257/412")).CCLS.) or (((("257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 11:31
-	3139	((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or (((("257/410") or ("257/411") or ("257/412")).CCLS.) or (((("257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.)) and (@rlad<19990429 or @pd<19990428)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 14:37
-	594	((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or (((("257/410") or ("257/411") or ("257/412")).CCLS.) or (((("257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.) and (@rlad<19990429 or @pd<19990428)) and (gate near10 (insulation or insulator or isolation or isolator))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 11:44
-	518	((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or (((("257/410") or ("257/411") or ("257/412")).CCLS.) or (((("257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.) and (@rlad<19990429 or @pd<19990428)) and (gate near10 (insulation or insulator or isolation or isolator)) and (silicon or polysilicon or polycrystalline near5 silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 11:50

-	377	(((((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or (((("257/410") or ("257/411") or ("257/412")).CCLS.) or (((("257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.)) and (@rlad<19990429 or @pd<19990428)) and (gate near10 (insulation or insulator or isolation or isolator))) and (silicon or polysilicon or polycrystalline near5 silicon)) and (doped or dopant or doping) ((((((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or (((("257/410") or ("257/411") or ("257/412")).CCLS.) or (((("257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.)) and (@rlad<19990429 or @pd<19990428)) and (gate near10 (insulation or insulator or isolation or isolator))) and (silicon or polysilicon or polycrystalline near5 silicon)) and (doped or dopant or doping)) and (oxygen or oxynitride or silicon adj dioxide)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 11:52
-	241	(((((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or (((("257/410") or ("257/411") or ("257/412")).CCLS.) or (((("257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.)) and (@rlad<19990429 or @pd<19990428)) and (gate near10 (insulation or insulator or isolation or isolator))) and (silicon or polysilicon or polycrystalline near5 silicon)) and (doped or dopant or doping)) and (oxygen or oxynitride or silicon adj dioxide)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 11:55
-	196	(((((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or (((("257/410") or ("257/411") or ("257/412")).CCLS.) or (((("257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.)) and (@rlad<19990429 or @pd<19990428)) and (gate near10 (insulation or insulator or isolation or isolator))) and (silicon or polysilicon or polycrystalline near5 silicon)) and (doped or dopant or doping)) and (oxygen or oxynitride or silicon adj dioxide) and (nitrogen or oxynitride or nitride)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 13:44
-	100	((("6277708") or ("6236094") or ("6191462") or ("6163050") or ("6133602") or ("6107657") or ("5962897") or ("5923056") or ("5886368") or ("5838051") or ("5831319") or ("5828111") or ("5811865") or ("5710454") or ("5635746") or ("5619051") or ("5614748") or ("5596214") or ("5565691") or ("5412246") or ("5289030") or ("5276346") or ("5268590") or ("5254867") or ("5237188") or ("5134451") or ("4954867") or ("4931411") or ("4855247") or ("4814854") or ("4698787") or ("3913211") or ("3863330") or ("3853633") or ("3724065")).PN.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 13:46
-	0	("L24 and silicon and oxygen and nitrogen and first.clm. and second.clm.").PN.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 13:47

		7	((("6277708") or ("6236094") or ("6191462") or ("6163050") or ("6133602") or ("6107657") or ("5962897") or ("5923056") or ("5886368") or ("5838051") or ("5831319") or ("5828111") or ("5811865") or ("5710454") or ("5635746") or ("5619051") or ("5614748") or ("5596214") or ("5565691") or ("5412246") or ("5289030") or ("5276346") or ("5268590") or ("5254867") or ("5237188") or ("5134451") or ("4954867") or ("4931411") or ("4855247") or ("4814854") or ("4698787") or ("3913211") or ("3863330") or ("3853633") or ("3724065")).PN.) and silicon and oxygen and nitrogen and first.clm. and second.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 13:50
		0	((("6277708") or ("6236094") or ("6191462") or ("6163050") or ("6133602") or ("6107657") or ("5962897") or ("5923056") or ("5886368") or ("5838051") or ("5831319") or ("5828111") or ("5811865") or ("5710454") or ("5635746") or ("5619051") or ("5614748") or ("5596214") or ("5565691") or ("5412246") or ("5289030") or ("5276346") or ("5268590") or ("5254867") or ("5237188") or ("5134451") or ("4954867") or ("4931411") or ("4855247") or ("4814854") or ("4698787") or ("3913211") or ("3863330") or ("3853633") or ("3724065")).PN.) and silicon and oxygen and nitrogen and first.clm. and second.clm.) and sion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 13:50
		1	((("6277708") or ("6236094") or ("6191462") or ("6163050") or ("6133602") or ("6107657") or ("5962897") or ("5923056") or ("5886368") or ("5838051") or ("5831319") or ("5828111") or ("5811865") or ("5710454") or ("5635746") or ("5619051") or ("5614748") or ("5596214") or ("5565691") or ("5412246") or ("5289030") or ("5276346") or ("5268590") or ("5254867") or ("5237188") or ("5134451") or ("4954867") or ("4931411") or ("4855247") or ("4814854") or ("4698787") or ("3913211") or ("3863330") or ("3853633") or ("3724065")).PN.) and silicon and oxygen and nitrogen and first.clm. and second.clm.) and silicon adj oxynitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 14:07
		0	((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or (((257/410) or ("257/411") or ("257/412")).CCLS.) or (((257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.) and (@rlad<19990429 or @pd<19990428)) and (silicon adj oxynitride with gate with insulation) and (side adj wall adj spacer with silicon with (oxide or dioxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 14:40
		0	((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or (((257/410) or ("257/411") or ("257/412")).CCLS.) or (((257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.) and (@rlad<19990429 or @pd<19990428)) and (silicon adj oxynitride with gate with insulation) and side adj wall adj spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 14:40

	0	((silicon adj oxynitride with gate with insulation) and side adj wall adj spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 14:59
	0	((silicon adj oxynitride or sion) with gate with insulation) and side adj wall adj spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 14:41
	0	((silicon adj oxynitride or sion) same gate same insulation) and side adj wall adj spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 14:42
	2	(((((257/356) or ("257/357") or ("257/359") or ("257/360")).CCLS.) or (((257/410") or ("257/411") or ("257/412")).CCLS.) or (((257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.)) and (@rlad<19990429 or @pd<19990428)) and silicon same oxy\$7 same (oxide or dioxide) same gate same ((side adj wall) near10 (silicon adj oxide or silicon adj dioxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 14:46
	5	(((((257/356) or ("257/357") or ("257/359") or ("257/360")).CCLS.) or (((257/410") or ("257/411") or ("257/412")).CCLS.) or (((257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.)) and (@rlad<19990429 or @pd<19990428)) and silicon same oxy\$7 same (oxide or dioxide) same gate same side adj wall	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 14:57
	0	(((((257/356) or ("257/357") or ("257/359") or ("257/360")).CCLS.) or (((257/410") or ("257/411") or ("257/412")).CCLS.) or (((257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.)) and (@rlad<19990429 or @pd<19990428)) and (gate adj insulation adj film same "sio:n")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 14:57
	0	(silicon adj oxinitride with gate with insulation) and side adj wall adj spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 14:59
	0	(silicon adj (oxynitride or oxinitride) with gate with insulation) and side adj wall adj spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 15:00
	137	(((((257/356) or ("257/357") or ("257/359") or ("257/360")).CCLS.) or (((257/410") or ("257/411") or ("257/412")).CCLS.) or (((257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.)) and (@rlad<19990429 or @pd<19990428)) and silicon same oxy\$7 same (oxide or dioxide) same gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 15:41
	9	gate.ti,ab. and oxynitride.ti,ab. and (side adj wall with silicon with \$oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 15:53

-	2022	side adj wall near10 (silicon adj oxide or silicon adj dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 15:55
-	80	side adj wall.ti. near10 (silicon adj oxide or silicon adj dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 15:56
-	89	side adj wall.ti. with (silicon adj oxide or silicon adj dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 15:56
-	3	side adj wall.ti. with (silicon adj oxide or silicon adj dioxide) and (silicon or polysilicon) adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 17:56
-	3	5620910.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 16:32
-	2	polysilicon adj gate.ti,ab. and (side adj wall adj spacer near10 silicon adj dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 16:46
-	2	polysilicon adj gate.ti,ab. and (side adj wall adj spacer near5 silicon adj dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 16:55
-	3	5620910.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 17:01
-	12	(tungsten adj silicide near5 gate adj electrode) and gate adj insulation adj film	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 17:03
-	3	5646054.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 17:56
-	50	(field adj oxide near5 nitrogen) and (257/\$5.ccls. or 438/\$5.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 20:20